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METHOD FOR FORMING A MIM (METAL-INSULATOR-METAL) CAPACITOR

ABSTRACT

Methods for forming a metal-insulator-metal (MIM) capacitor using an organic anti-reflective coating (ARC) are described. The first electrode of the MIM capacitor is formed from a first metal layer. The organic ARC is applied, and the second electrode of the MIM capacitor is formed from a second metal layer. The organic ARC is then removed using a nominal clean technique. Because the organic ARC is removed, the performance of the MIM capacitor is improved. Specifically, the breakdown voltage of the MIM capacitor increases and the leakage current decreases.

FIGURE 5C



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